

# **Structured Electronic Design**

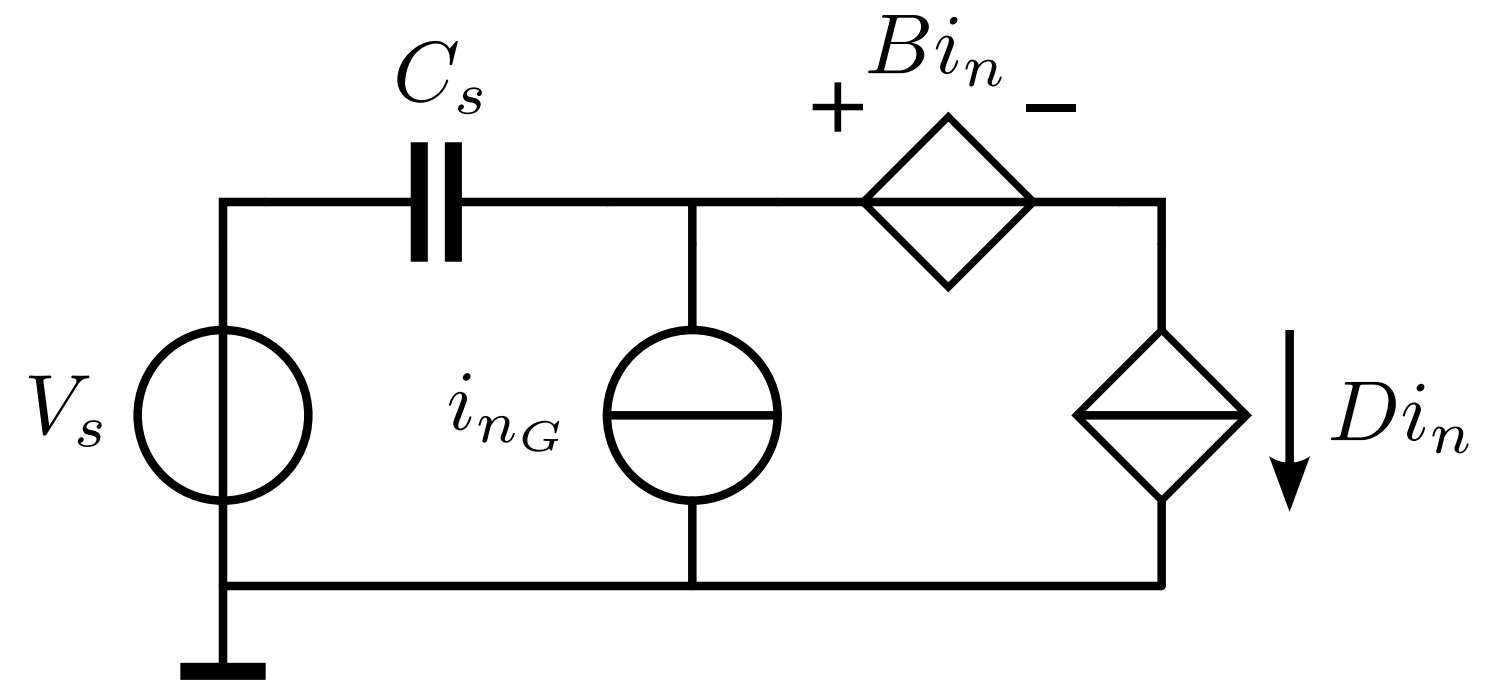
CS stage:

Noise optimization with a capacitive voltage source

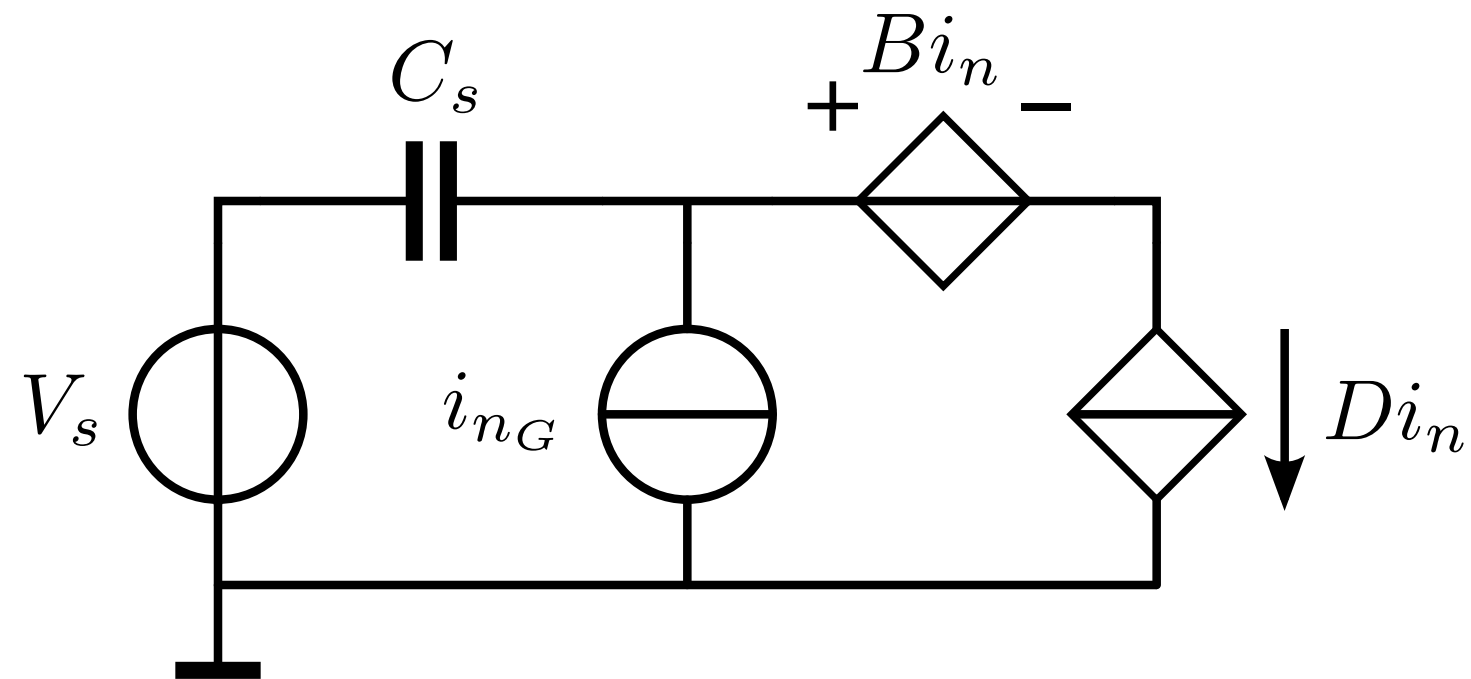
*Anton J.M. Montagne*

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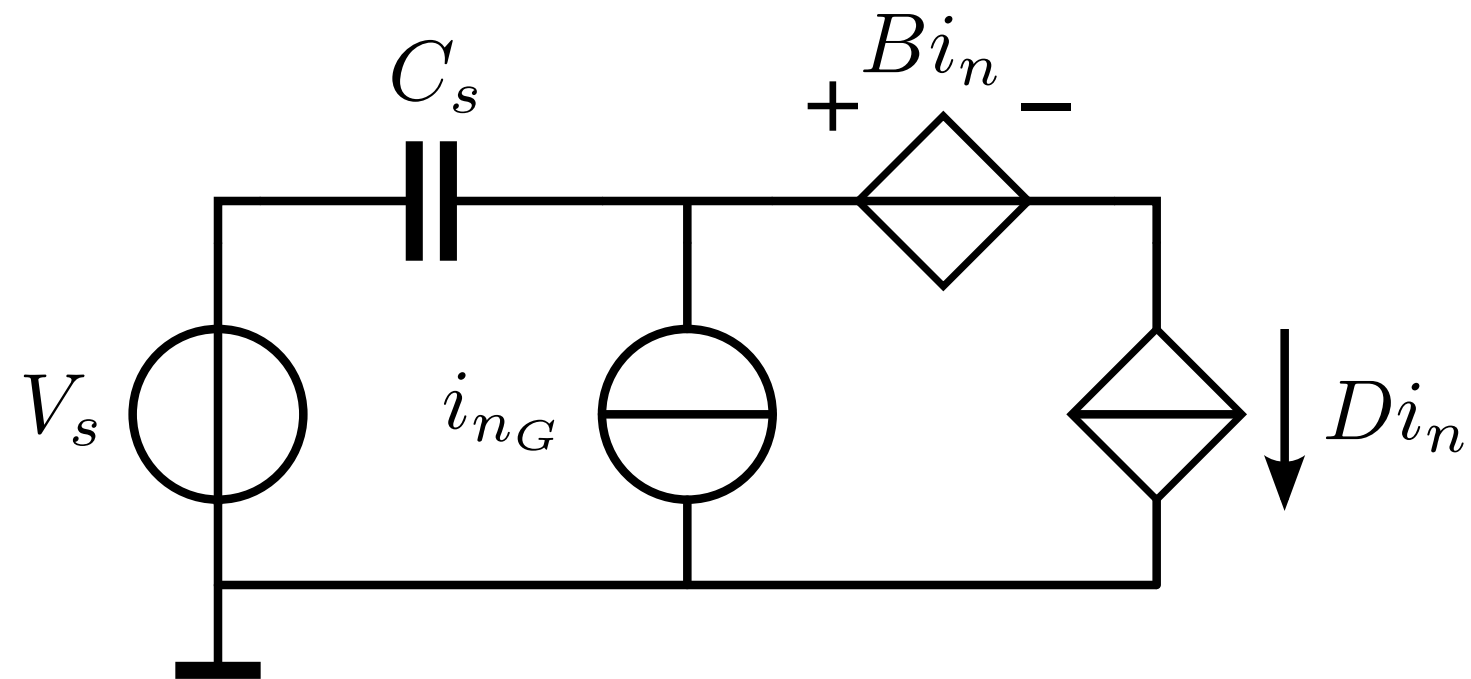
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$$S_{i_{nG}} = 2qI_G$$

$$B = -\frac{1}{g_m}$$

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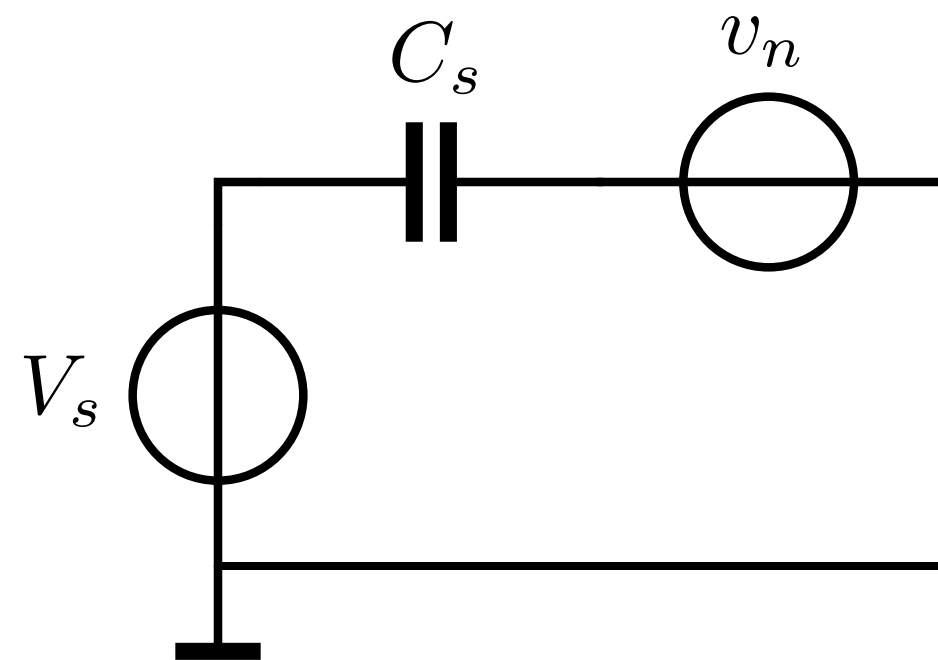


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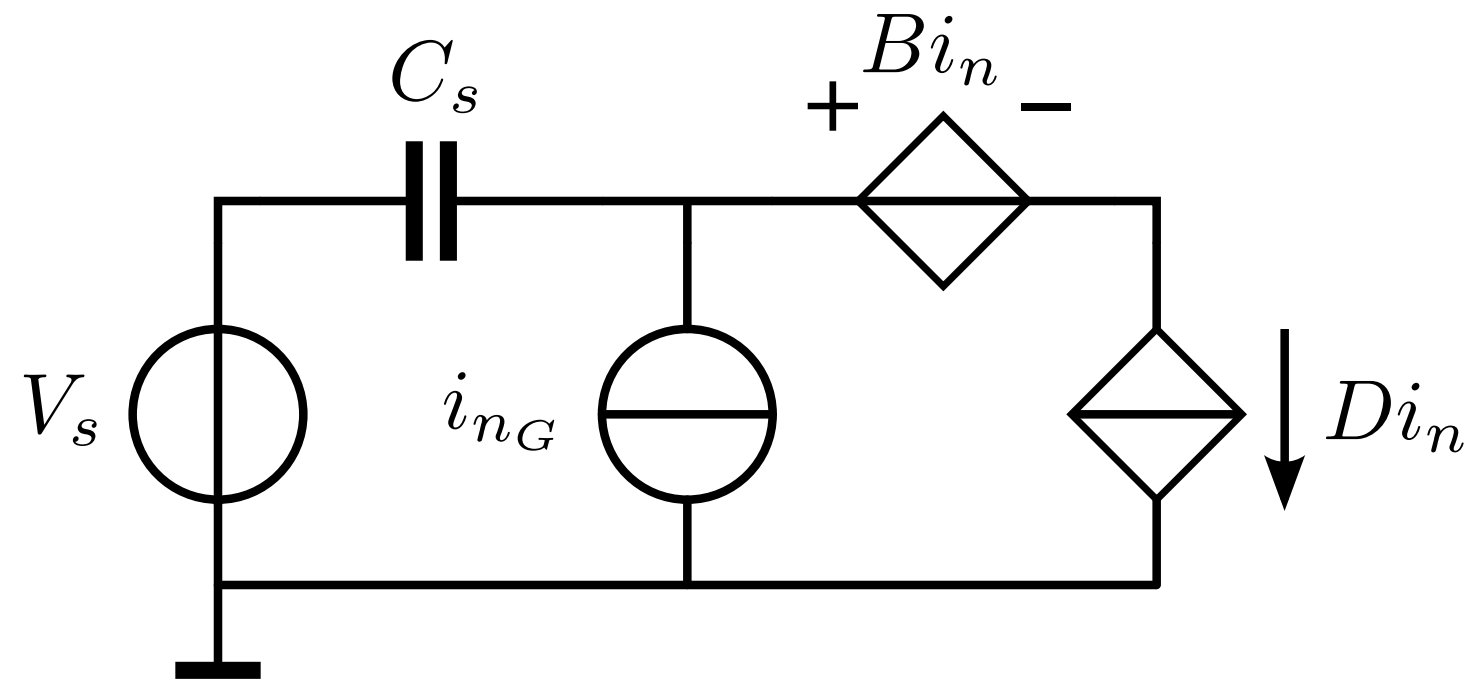
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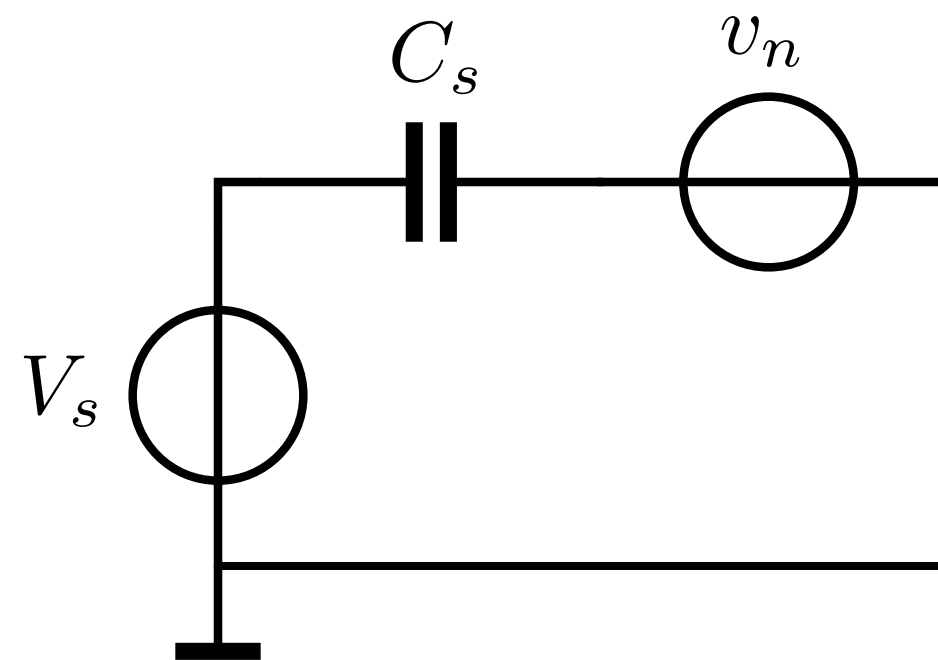


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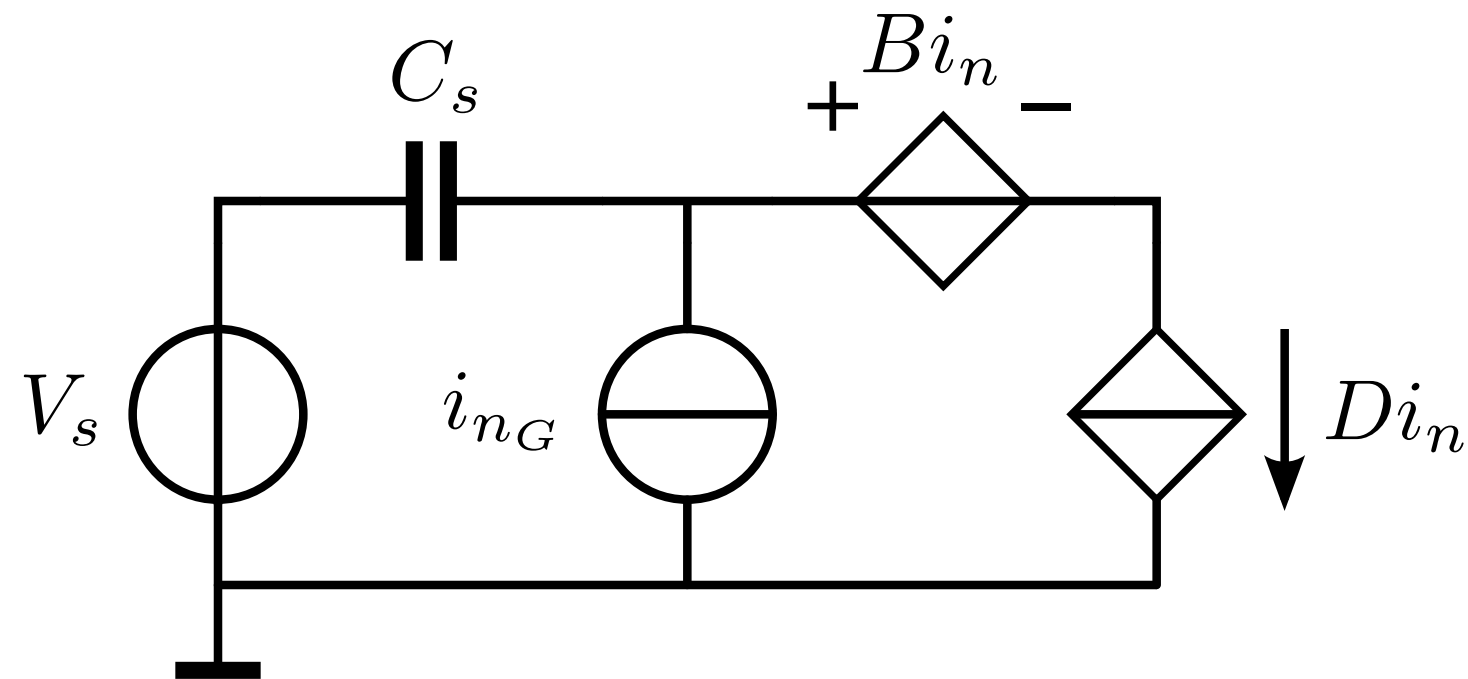
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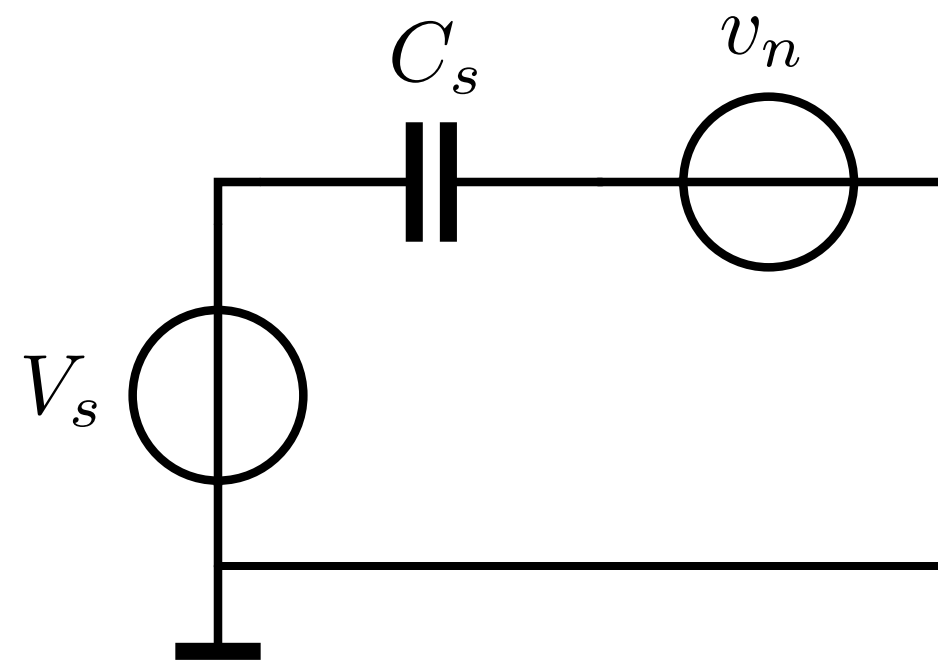


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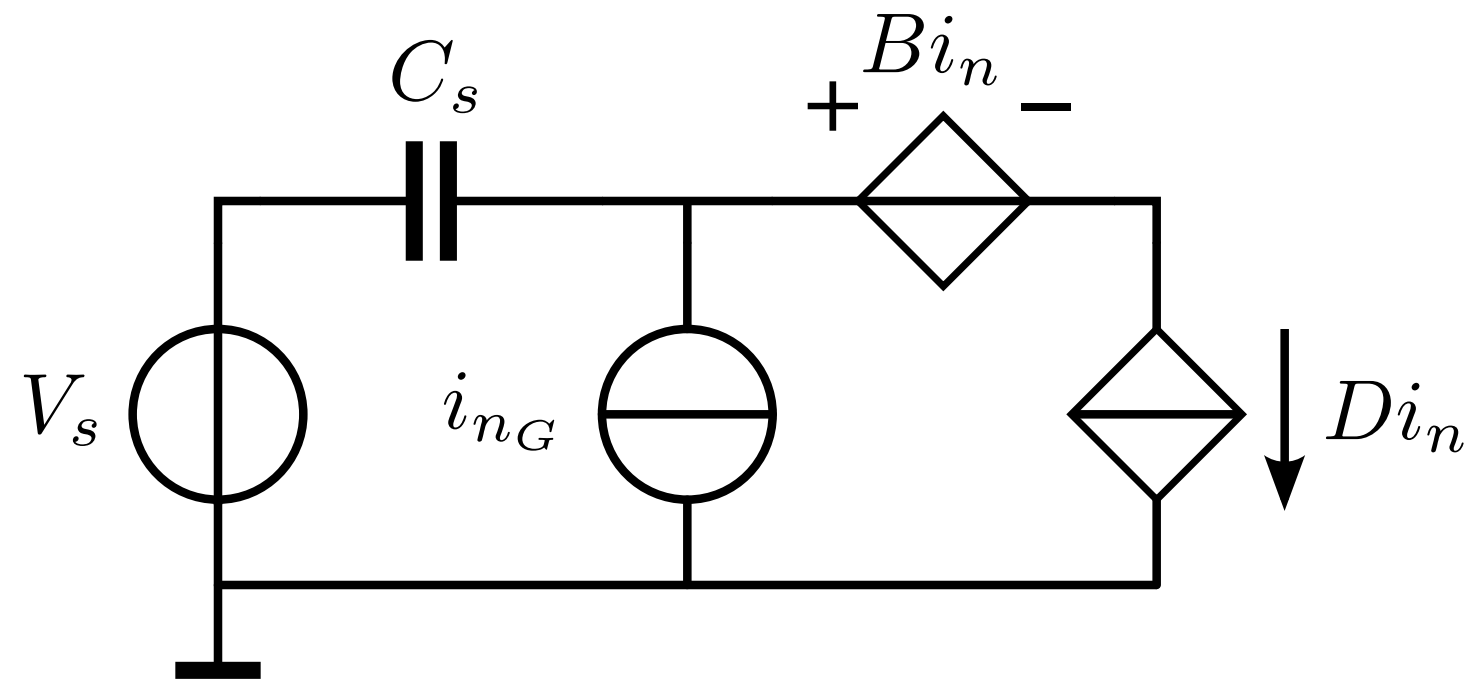
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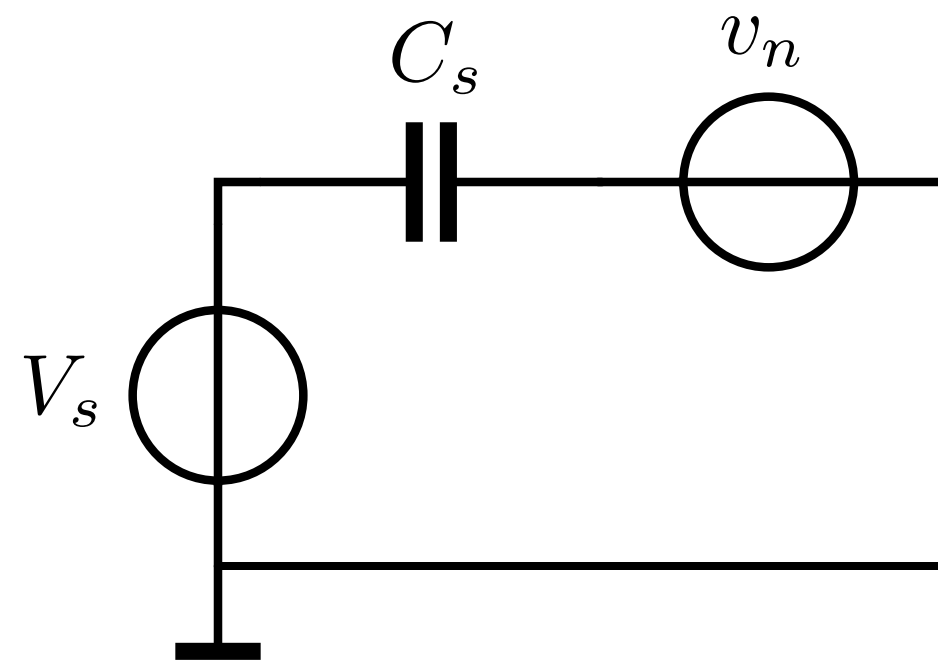


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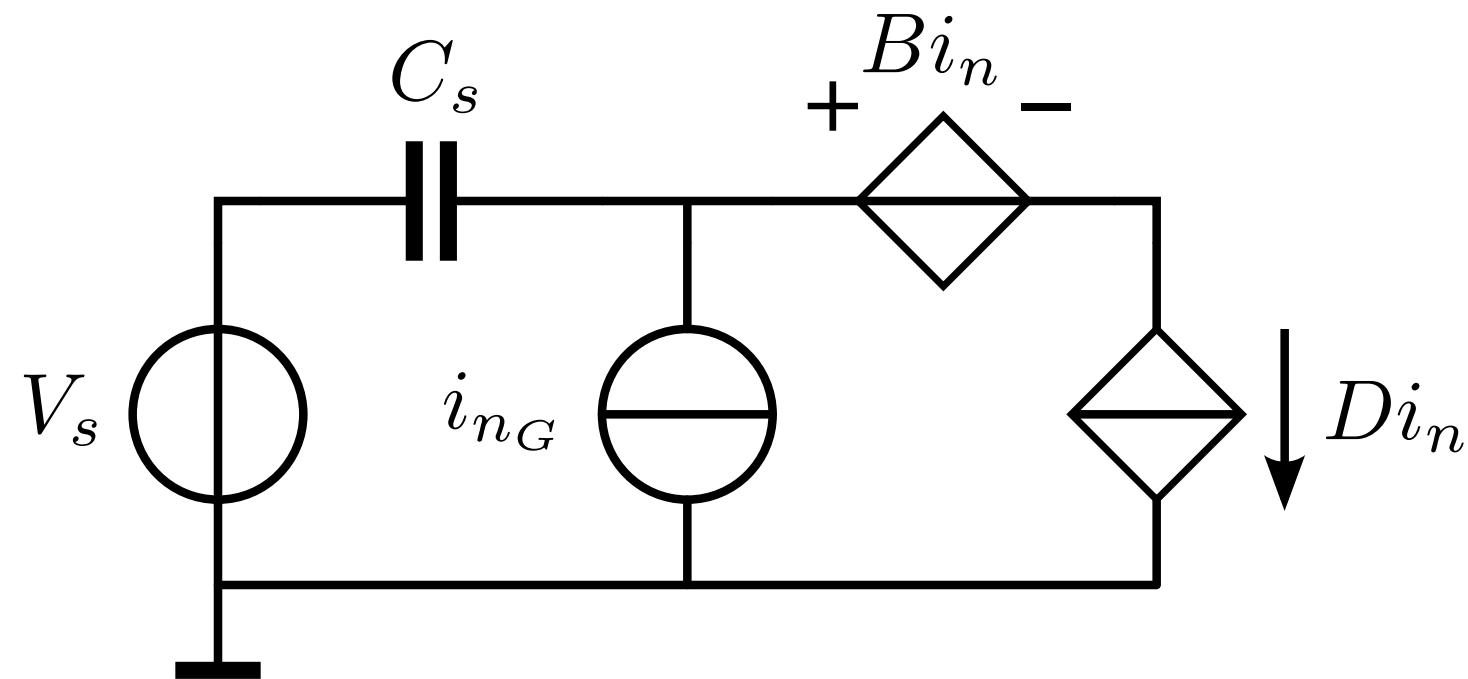
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Similar as with resistive source:



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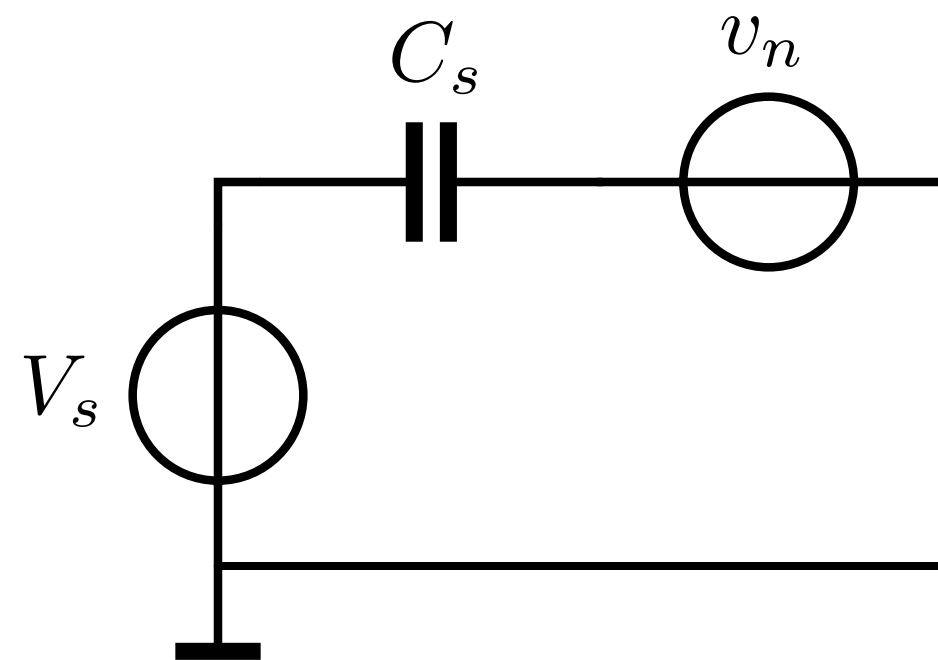


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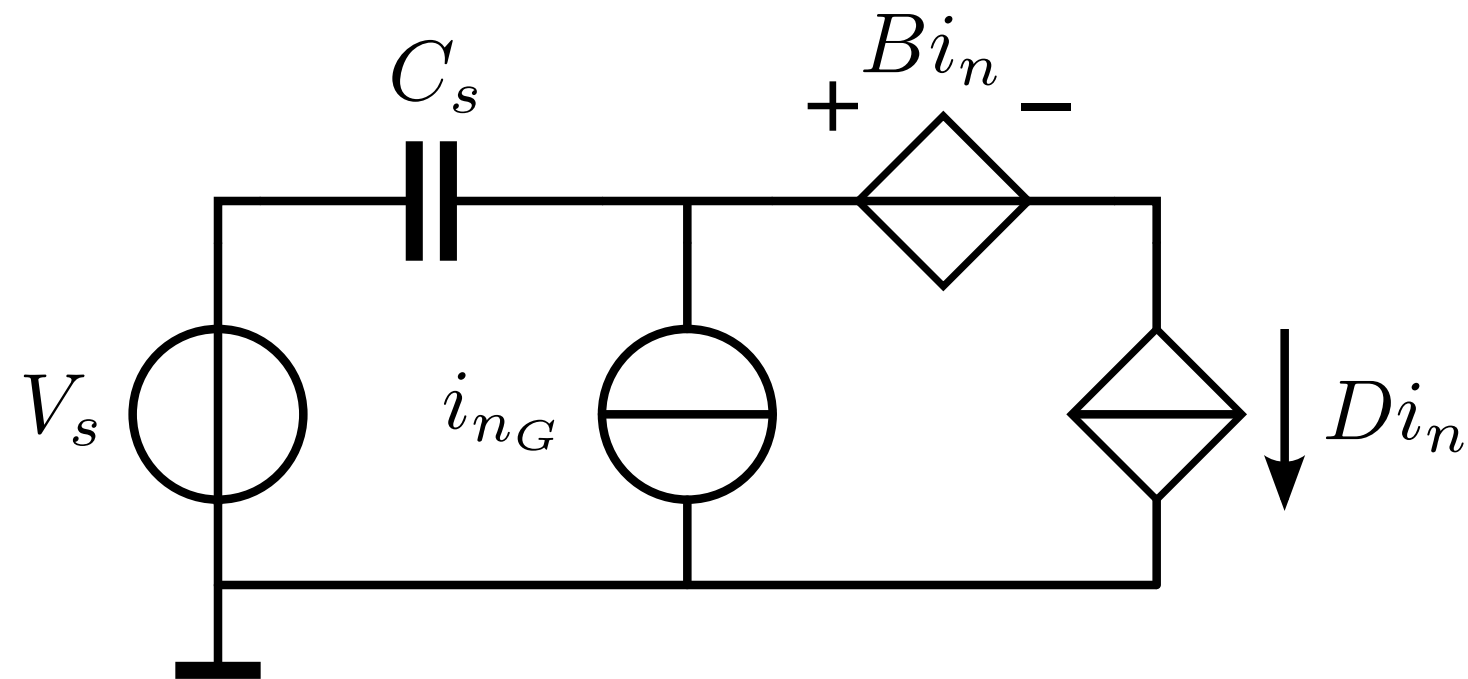
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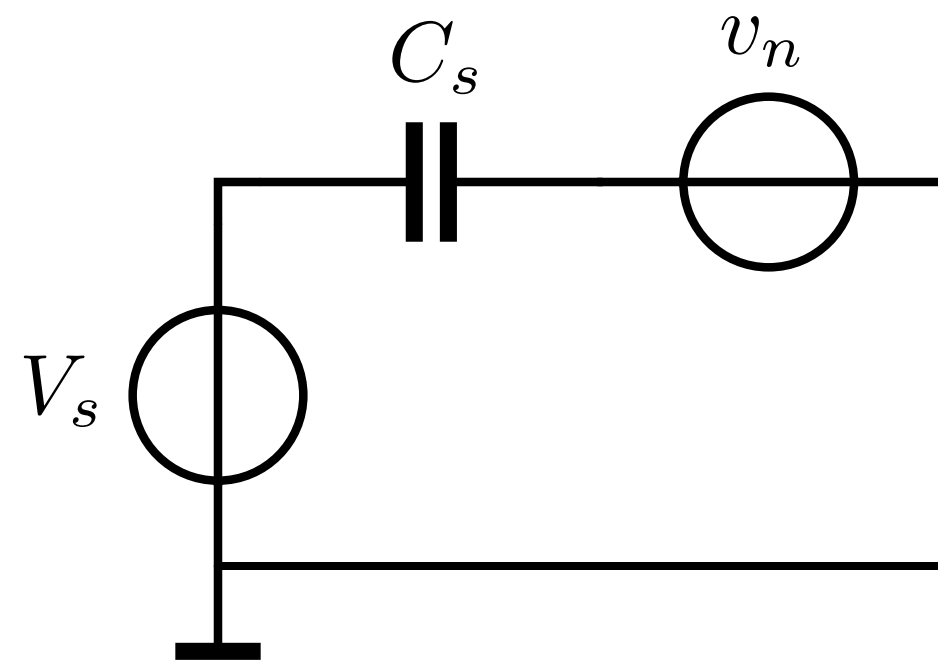


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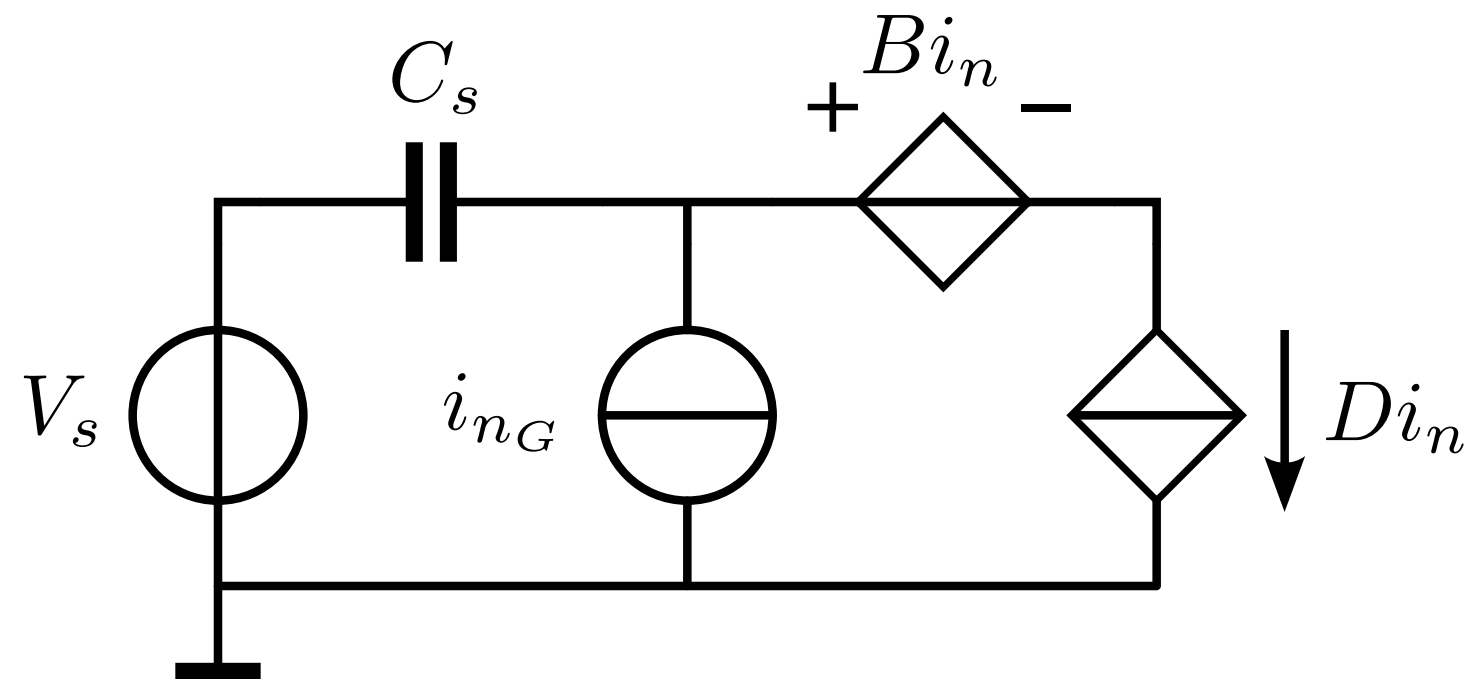
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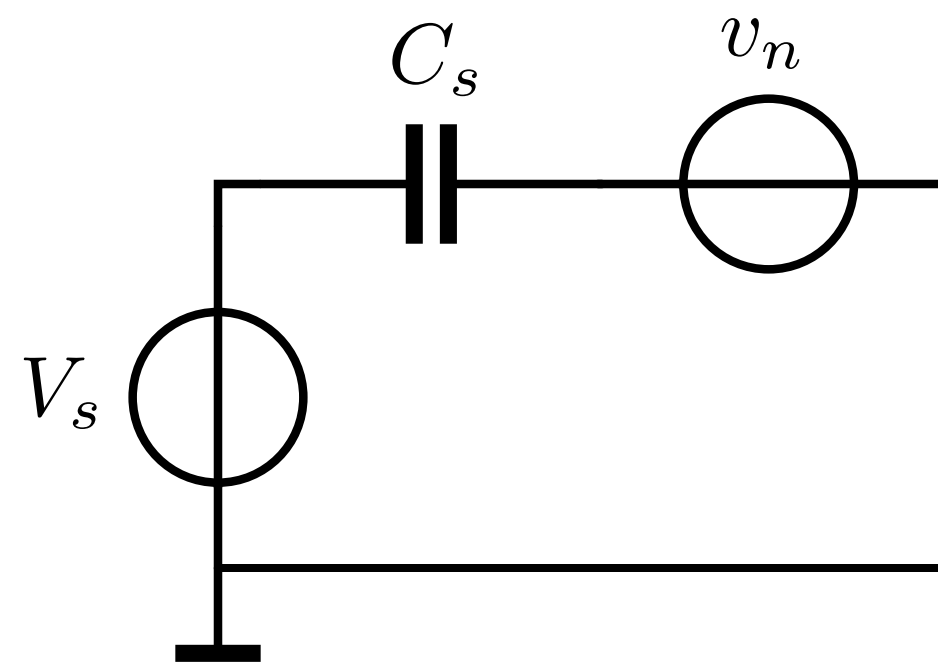


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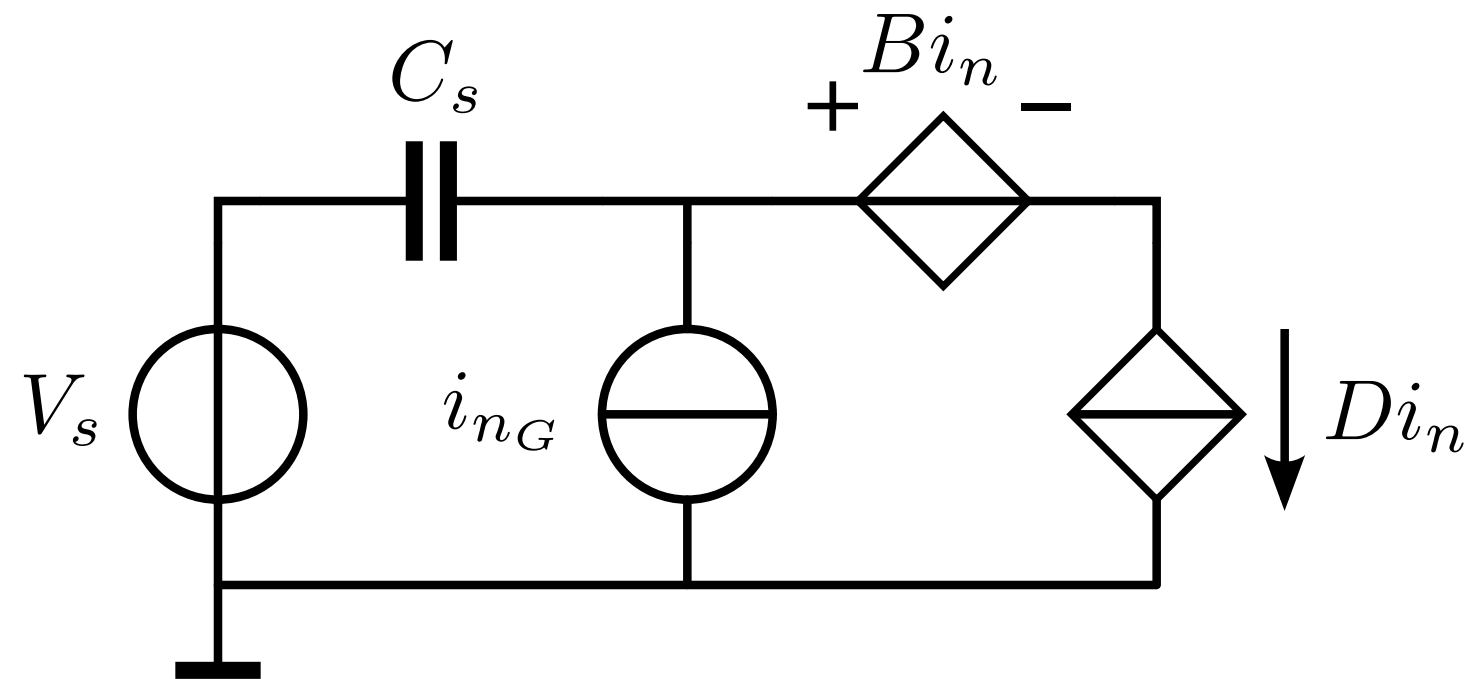
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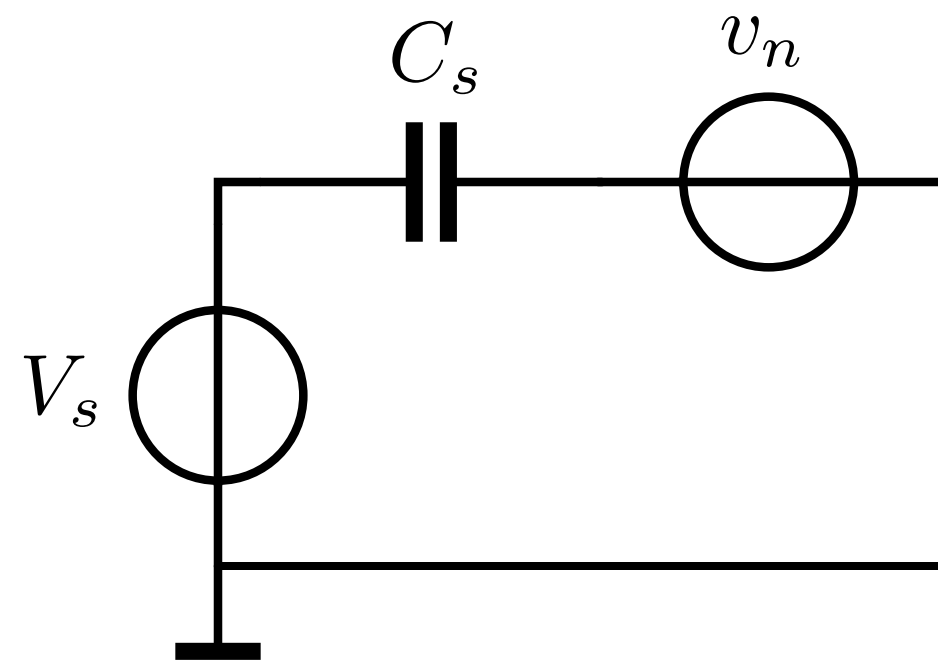


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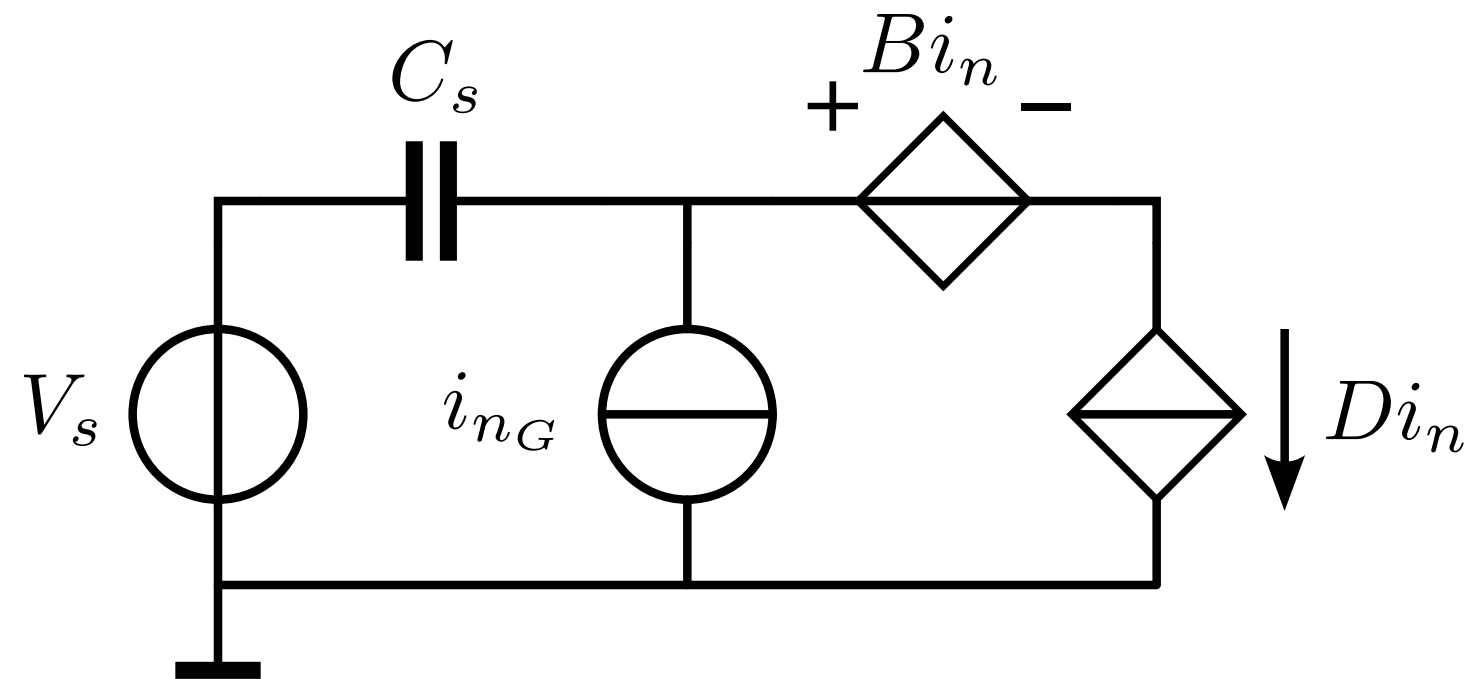
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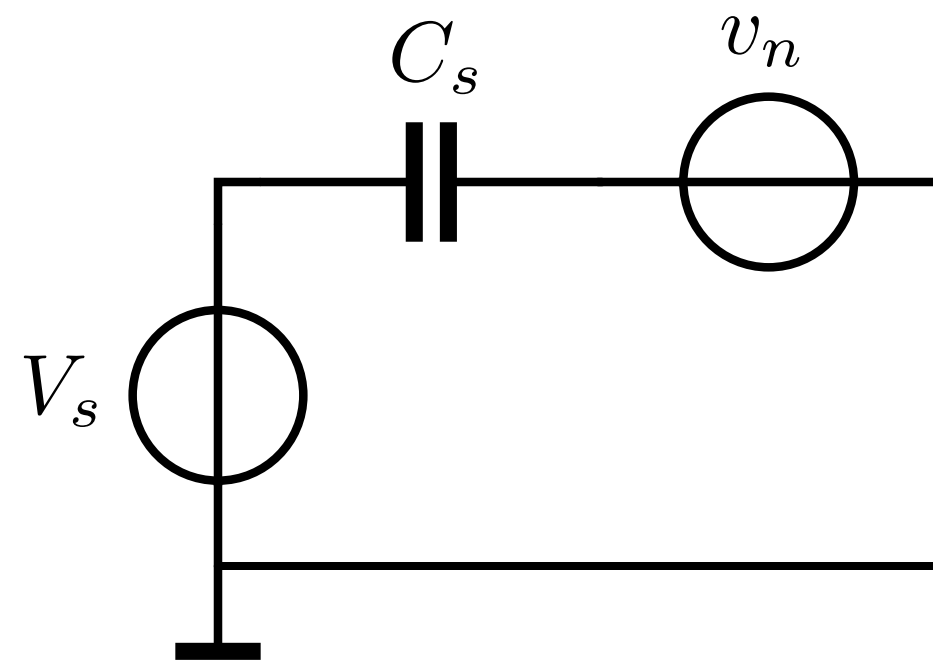


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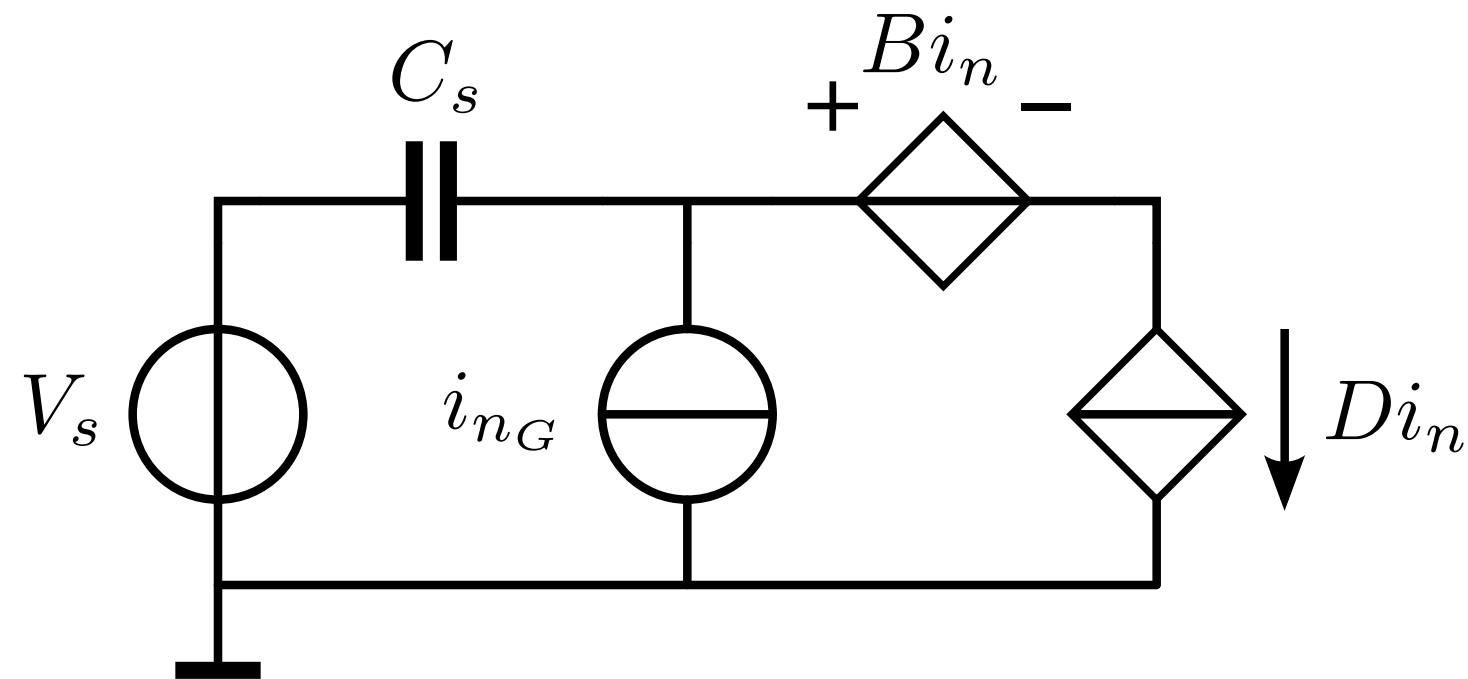
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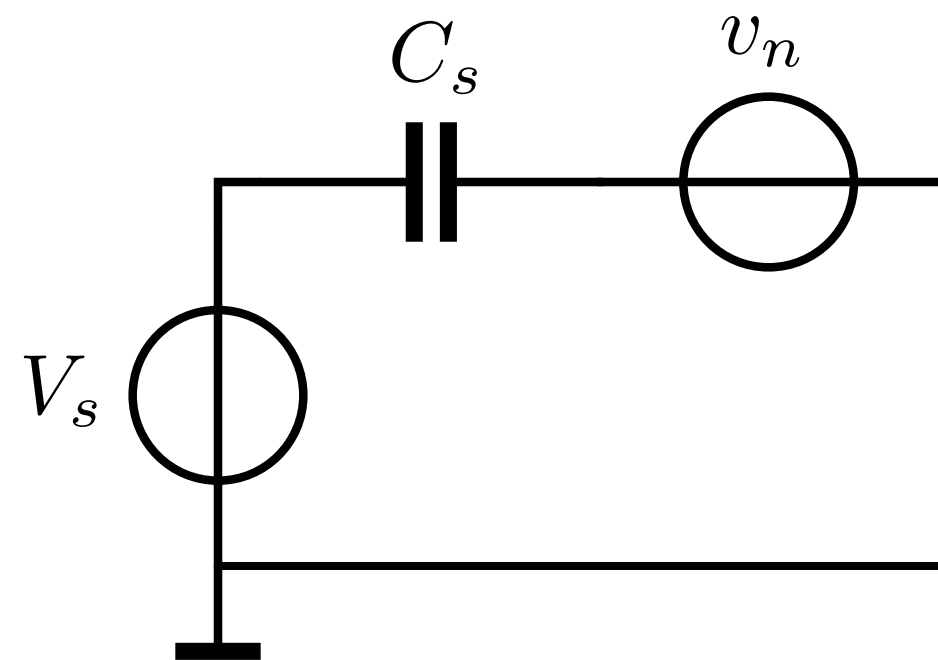


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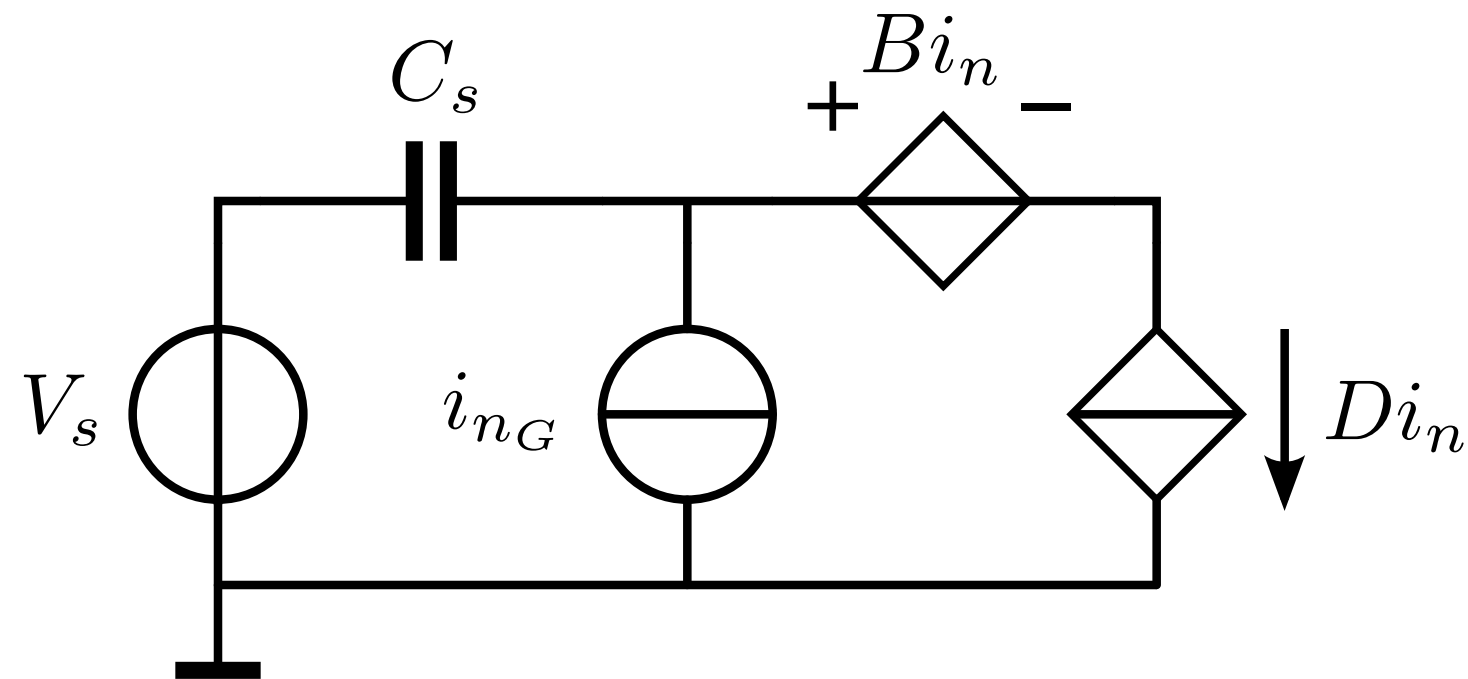
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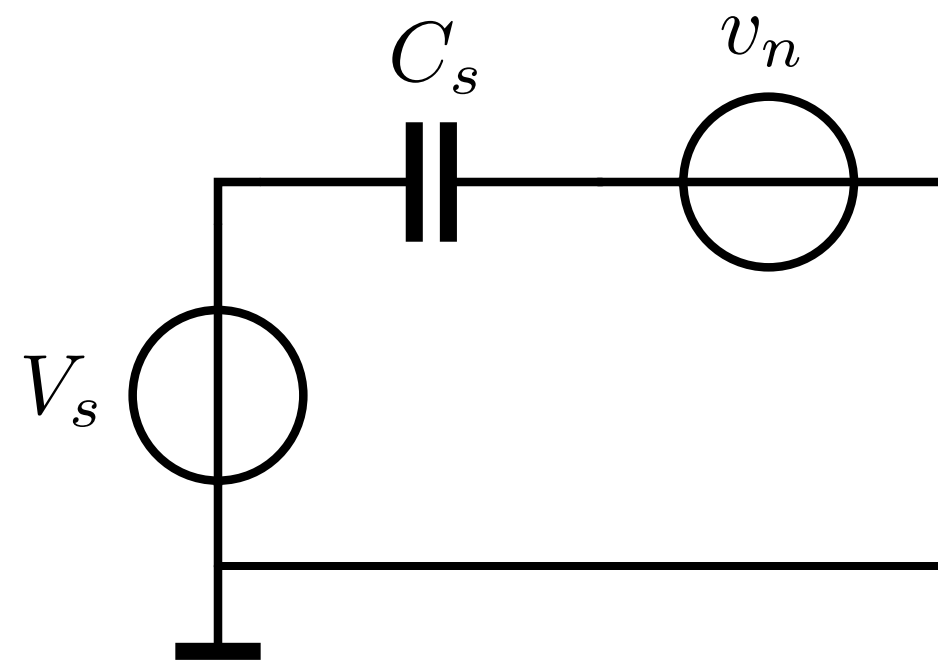


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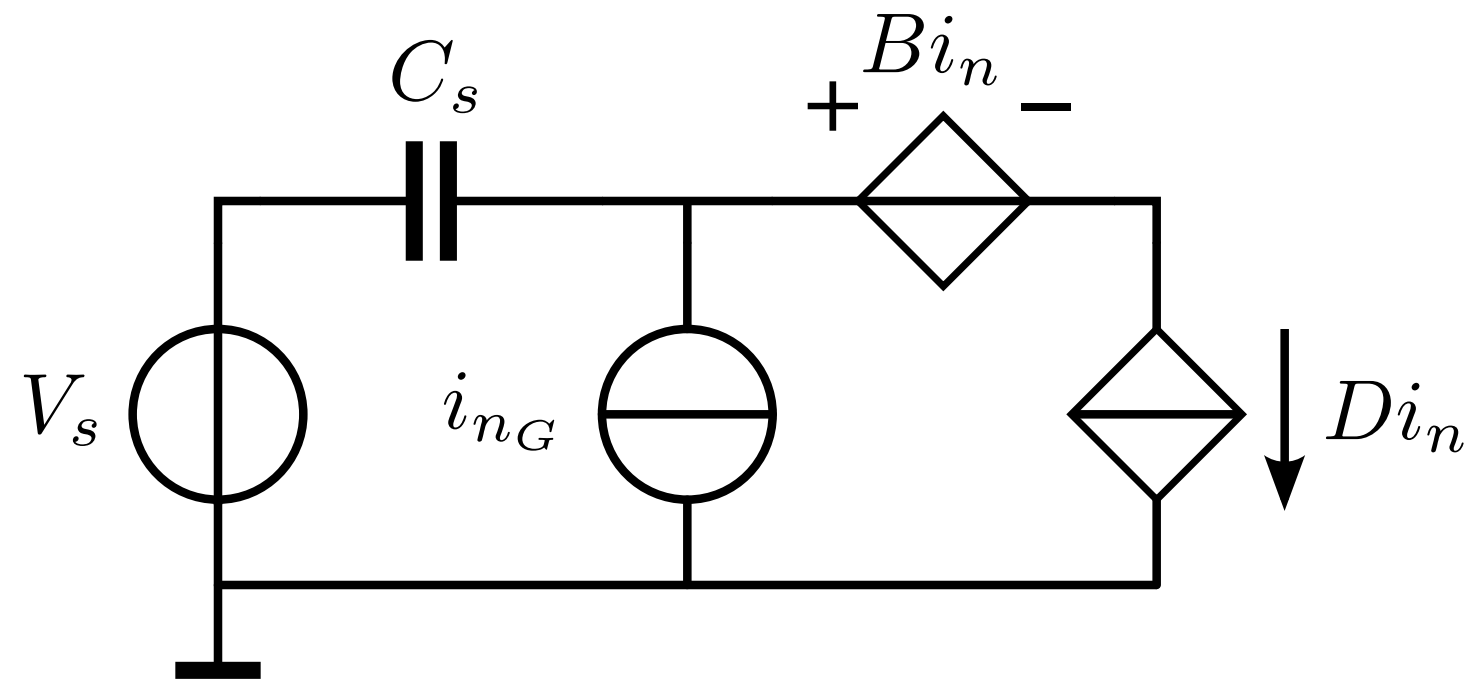


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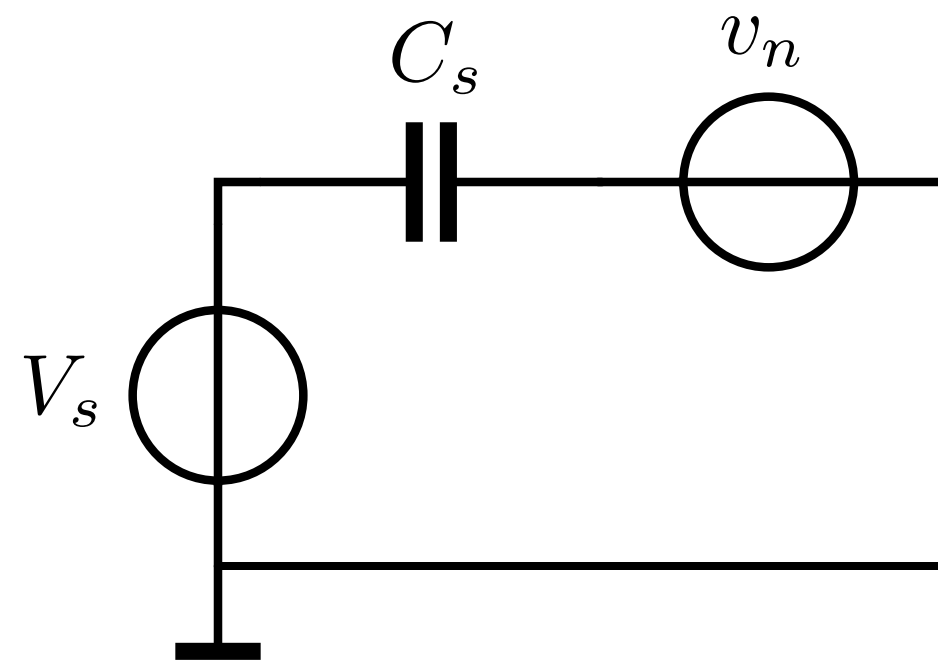


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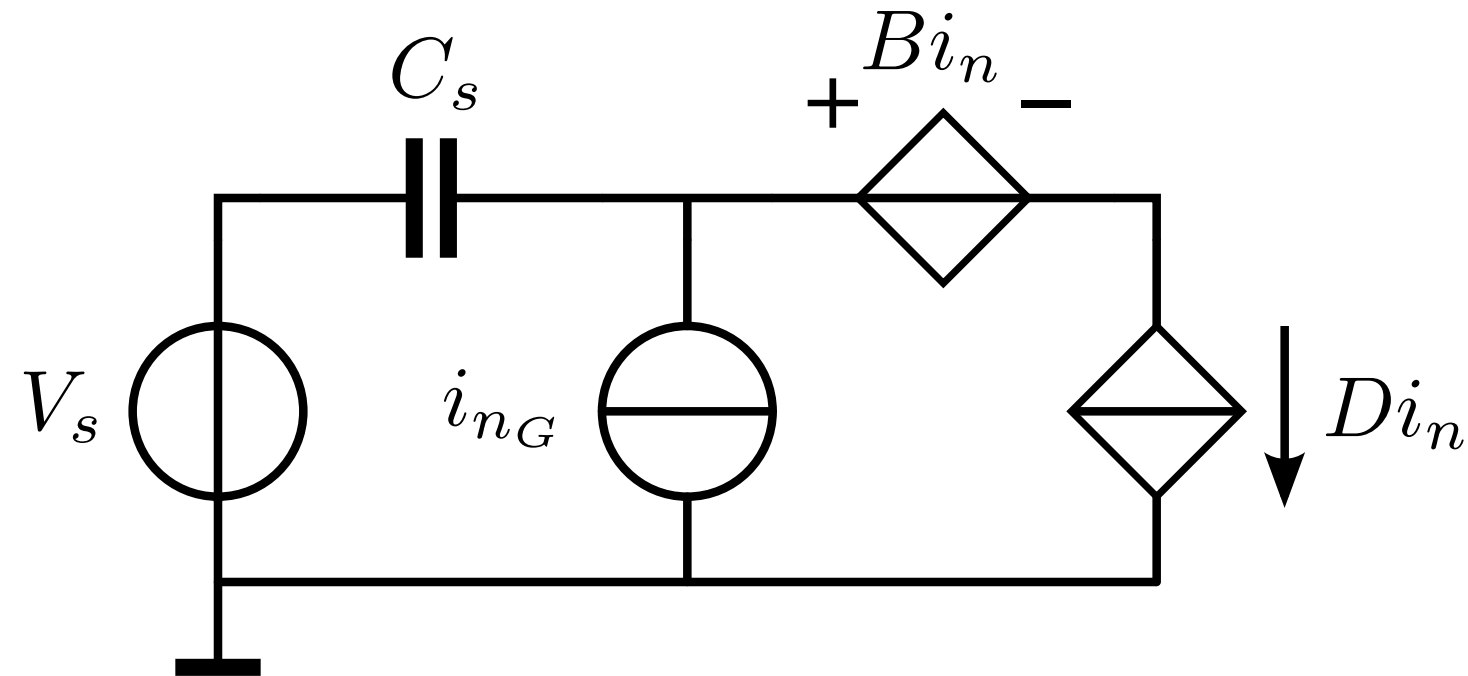
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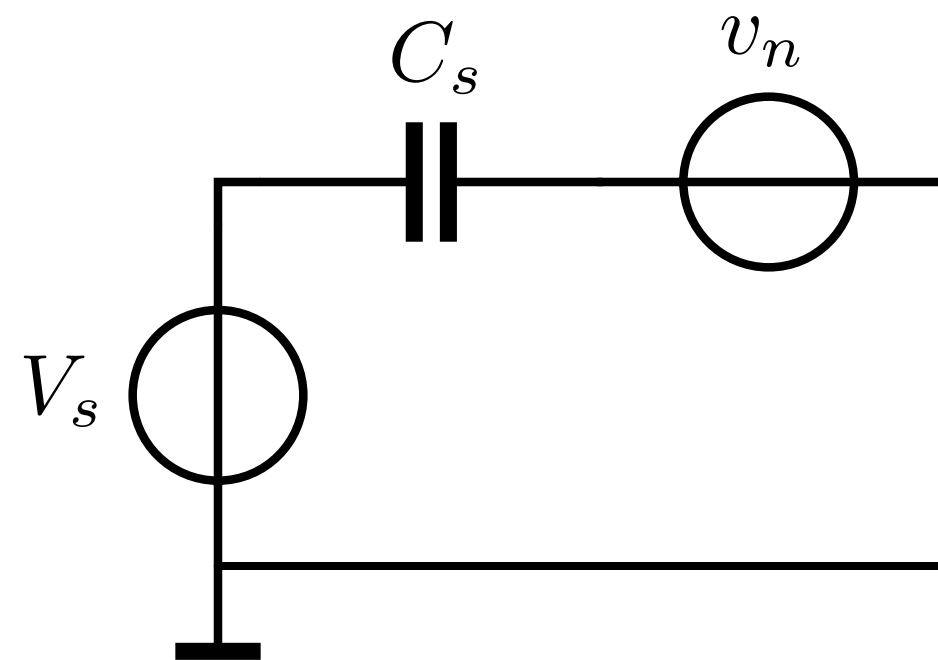


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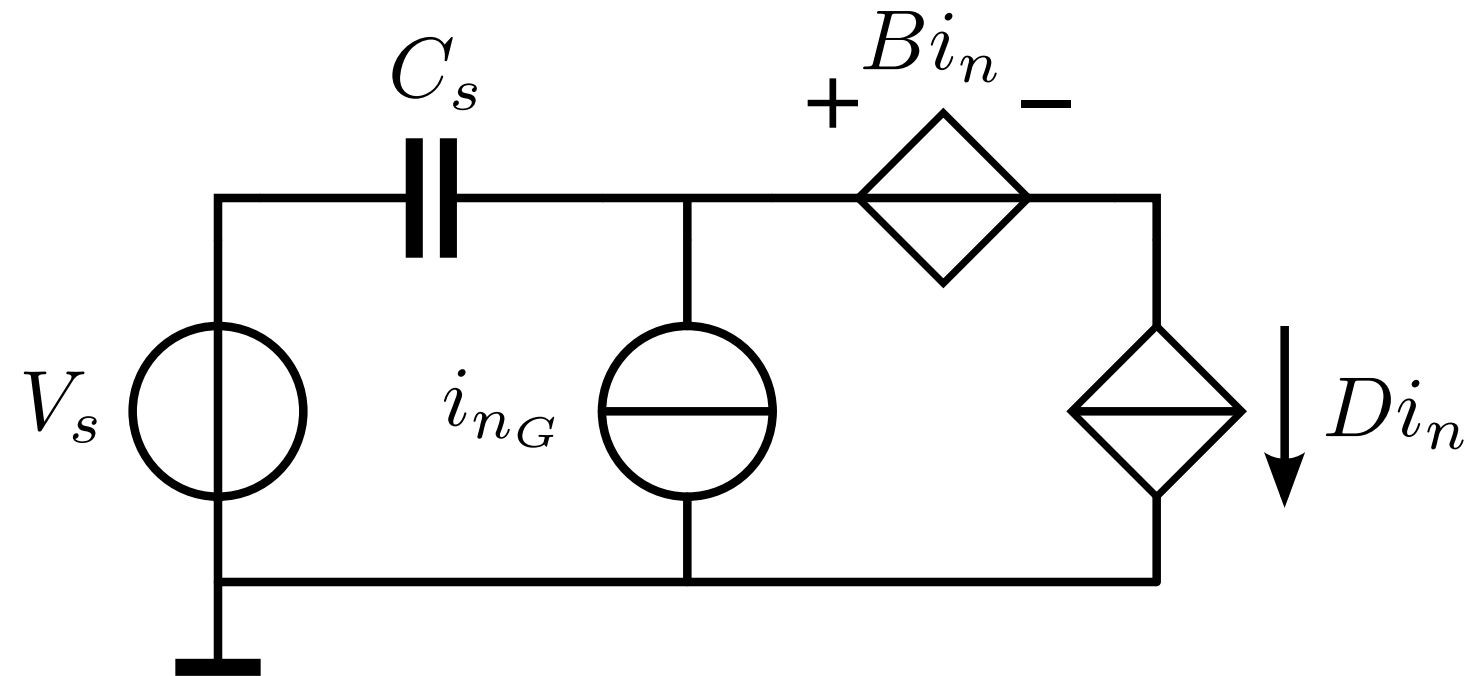
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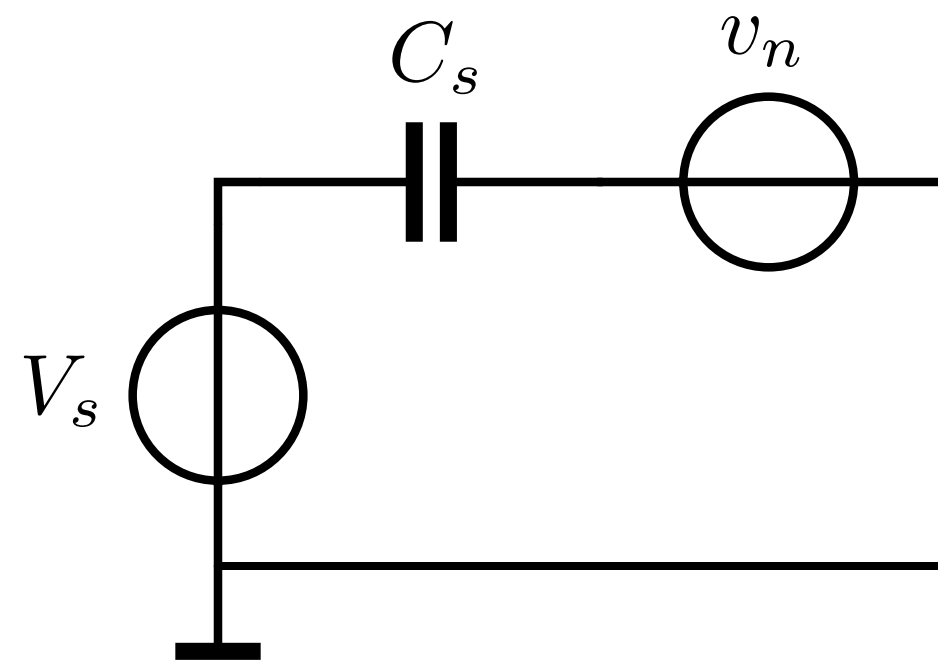


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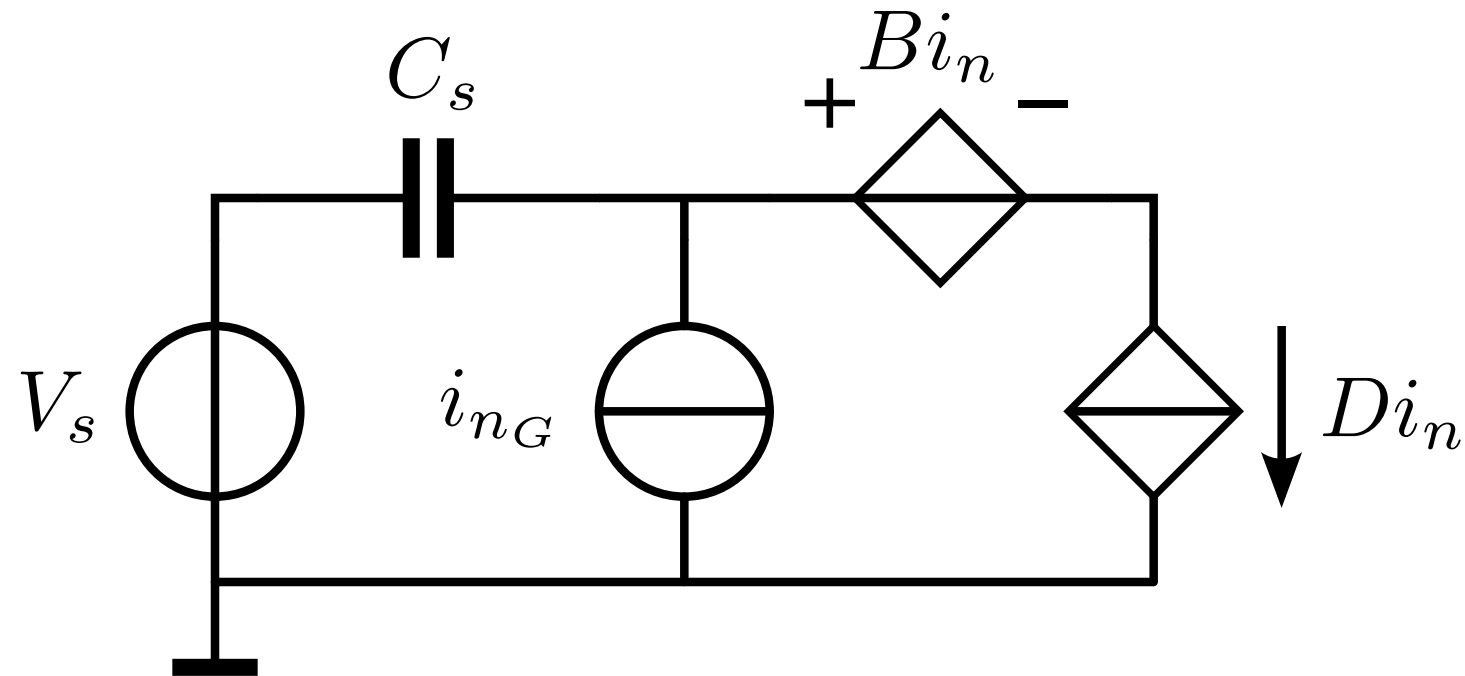
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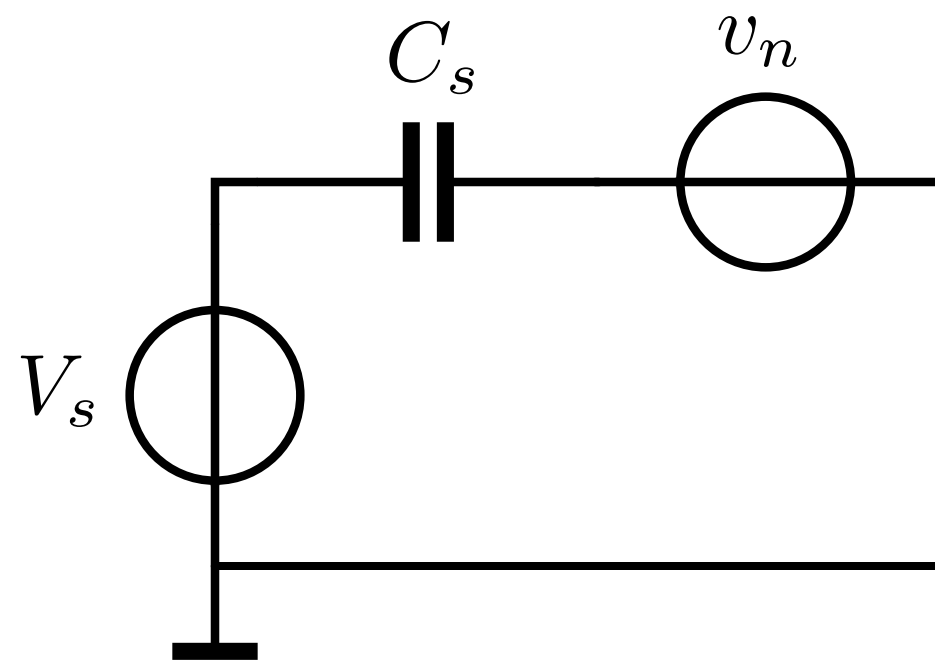


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